

SS32 THRU SS320

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER
Reverse Voltage - 20 to 200 Volts Forward Current - 3.0 Amperes

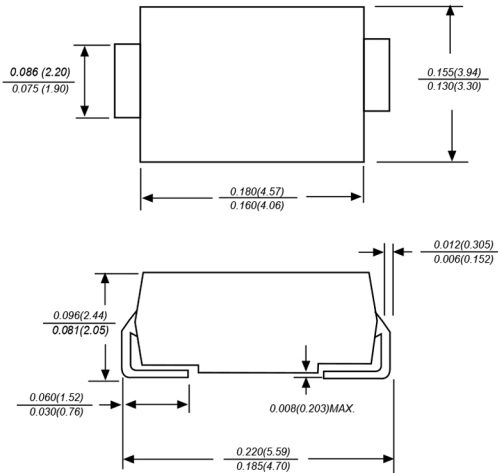
FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 250°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC DO-214AC molded plastic body
Terminals: leads solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: .09 grams

DO-214AA



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

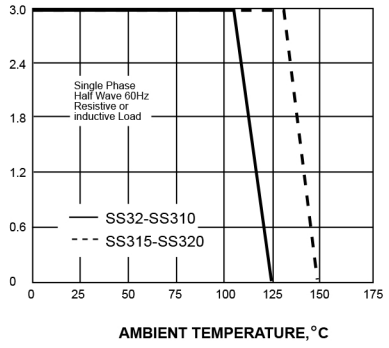
Ratings at 25°C ambient temperature unless otherwise specified.
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	SS32	SS33	SS34	SS35	SS36	SS38	SS310	SS315	SS320	UNITS	
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	VOLTS	
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum average forward rectified current at T_L (see fig. 1)	$I_{(AV)}$	3.0									Amps	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	70.0									Amps	
Maximum instantaneous forward voltage at 3.0A	V_F	0.55		0.70		0.85		0.95		Volts		
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	20			0.5			10		1.0	mA	
Typical junction capacitance (NOTE 1)	C_J	500			300						pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	55.0			62.0					$^\circ\text{C/W}$		
Operating junction temperature range	T_J	-65 to +125			-65 to +150						$^\circ\text{C}$	
Storage temperature range	T_{STG}	-65 to +150										$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

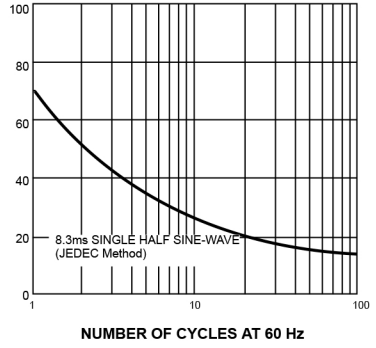
AVERAGE FORWARD RECTIFIED CURRENT,
 AMPERES

FIG. 1-FORWARD CURRENT DERATING CURVE



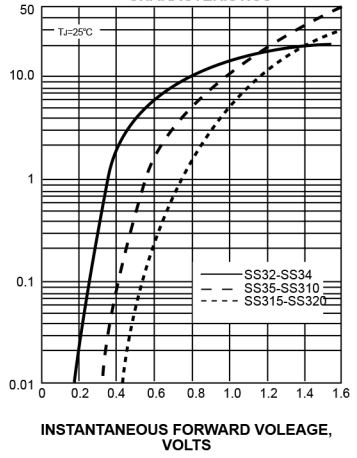
PEAK FORWARD SURGE CURRENT,
 AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



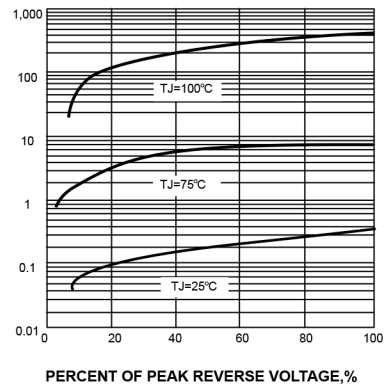
INSTANTANEOUS FORWARD CURRENT, AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



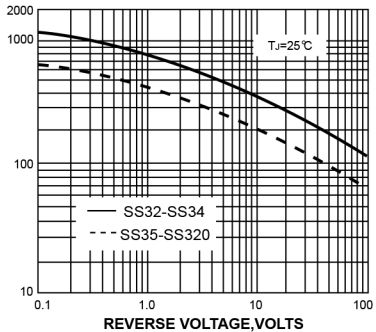
INSTANTANEOUS REVERSE CURRENT,
 MILLIAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



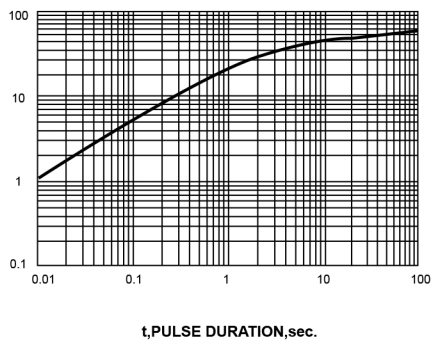
JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE,
 °C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



单击下面可查看定价，库存，交付和生命周期等信息

[>>RCD\(达标电子\)](#)